

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device comprising:

providing a substrate having an insulating layer and a single crystal silicon layer formed on the insulating layer;

forming a strain-inducing semiconductor layer on the single crystal silicon layer, the strain-inducing semiconductor having ~~the-a~~ lattice constant differing from ~~the-a~~ lattice constant of the single crystal silicon layer;

matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer and changing the single crystal silicon layer into a strained silicon layer, by providing an annealing process with respect to the single crystal silicon layer and the strain-inducing semiconductor layer without performing ion implantation in the single crystal silicon layer and the strain-inducing semiconductor layer by matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer; and

removing the strain-inducing semiconductor layer.

2. (Canceled)

3. (Currently amended) The method of manufacturing a semiconductor device as defined in claim 1,

wherein ~~when-athe~~ single crystal silicon layer is provided with the strain-inducing semiconductor layer formed on the strain-inducing semiconductor layer thereon, wherein the single crystal silicon layer ~~on the strain inducing semiconductor layer~~ has a thickness ~~which causes no defects~~such that no defect occurs in the strain-inducing semiconductor layer.

4. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein a layer including germanium is formed as the strain-inducing semiconductor layer.

5. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein the strain-inducing semiconductor layer is removed by wet etching using mixed acid of hydrofluoric acid and nitric acid.

6. (Original) The method of manufacturing a semiconductor device as defined in claim 1,

wherein the step of forming the strain-inducing semiconductor layer is performed by using a metal organic chemical vapor deposition method, a molecular beam epitaxy method, or a ultra high vacuum chemical vapor deposition method.

7. (Currently Amended) The method of manufacturing a semiconductor device as defined in claim 2claim 1,

wherein the annealing process is performed through a temperature increase process, a constant temperature process, and a temperature decrease process.

8. (Withdrawn) A semiconductor device comprising:
a semiconductor substrate manufactured by the method of manufacturing a semiconductor device as defined in claim 1.

9. (Withdrawn) A semiconductor device comprising:
a semiconductor substrate which includes an insulating layer and a strained silicon layer formed on the insulating layer; and
a field effect transistor formed on the semiconductor substrate.

10. (New) A method of manufacturing a semiconductor device comprising:

providing a substrate having an insulating layer and a single crystal silicon layer formed on the insulating layer;

forming a strain-inducing semiconductor layer on the single crystal silicon layer, the strain-inducing semiconductor having a lattice constant differing from a lattice constant of the single crystal silicon layer;

changing the single crystal silicon layer into a strained silicon layer, by cutting a Si-Si bond of the single crystal silicon layer through providing an annealing process and matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer; and

removing the strain-inducing semiconductor layer.